

Part Number

Customer

| Category | Parameter | Specification | Measurement Method | |
|---------------|-----------|---|---------------------------------|-----------------------------|
| OverallWafer | 1.0 | Diameter | 100.00 +/- 0.30 mm | |
| | 2.0 | Primary Flat Orientation | {110} +/- 1 | Wafer Vendor |
| | 3.0 | Primary Flat Length | 32.50 +/- 2.50 mm | Wafer Vendor |
| | 4.0 | Secondary Flat Length | 18.00 +/- 2.00 mm @ 90+/- 5 deg | |
| | 5.0 | Overall Thickness | 800.00 +/- 25.00 μ m | ADE, 100% |
| | 6.0 | Total Thickness Variation (TTV) | <4.00 μ m | Guaranteed by Process |
| | 7.0 | Bow | <40.00 μ m | ADE to ASTM F534, 20% |
| | 8.0 | Warp | <40.00 μ m | ADE to ASTM F657, 20% |
| | 9.0 | Edge Chips | None | Bright Light, 100% (note 2) |
| | 10.0 | Edge Exclusion | 5mm | |
| HandleSilicon | 11.0 | Frontsurface condition | Polished | Bright Light, 100% (note2) |
| | 12.0 | Backsurface condition | Etched | Bright Light, 100% (note2) |
| | 13.0 | Handle Silicon Raw Material | Prime Silicon | |
| | 14.0 | Handle Growth Method | CZ | Wafer Vendor |
| | 15.0 | Handle Orientation | {100} +/- 0.5 | Wafer Vendor |
| | 16.0 | Handle Thickness | 800.00 +/- 25.00 μ m | ADE, 100% |
| | 17.0 | Handle Doping Type | P | Wafer Vendor |
| | 18.0 | Handle Dopant | Boron | Wafer Vendor |
| | 19.0 | Handle Resistivity | 0.015 ~ 0.020 | Wafer Vendor |
| | 19.1 | Handle Silicon Dislocation Etch Pit Density | <100/cm ² | Wafer Vendor |
| | 20.0 | Surface Haze | None | Bright Light, 100% (note 2) |

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|------------------|-------------------|---|
| Shipping Details | Wafer per box : | Max 25 |
| | Packaging : | Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging |
| | Lot Shipment Data | Device Thickness Bow / Warp Data Handle and SOI Thickness |



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information